

ABSTRACT OF THE DISCLOSURE

A method of stabilizing parasitic capacitance in an LCD device. Pluralities of transversely expanding gate lines are formed on a substrate. A first insulating layer is formed on the substrate and the gate lines. By performing a photolithography procedure using a photomask, a plurality of longitudinally expanding data lines and a plurality of metallic light shield layers are formed on part of the first insulating layer, wherein the metallic light shield layers are located on both sides of the data line. A second insulating layer is formed on the metallic light shield layers and the data lines. Transparent conductive layers are formed on part of the second insulating layer. Moreover, conductive plugs penetrating the second insulating layer are formed to electrically connect the metallic light shield layers and the transparent conductive layers.